

Briefs: Micron has memory for entry-level phones

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Micron Technology has developed a memory device for so-called entry-level cell phones that play a major role in developing-nation markets.

Micron says the device will allow producers to keep costs as low as possible to make phones more affordable in developing countries.

Officially, the device is known as x16 burst A/D multiplexed pseudo-SPRAM, or PSRAM, and includes a 30-percent reduction in address and data pins that allows for simplified manufacturing and is incorporated into Micron's CellularRAM device for low-cost handsets.

Micron plans to begin volume production of the device in the first quarter of 2006.

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